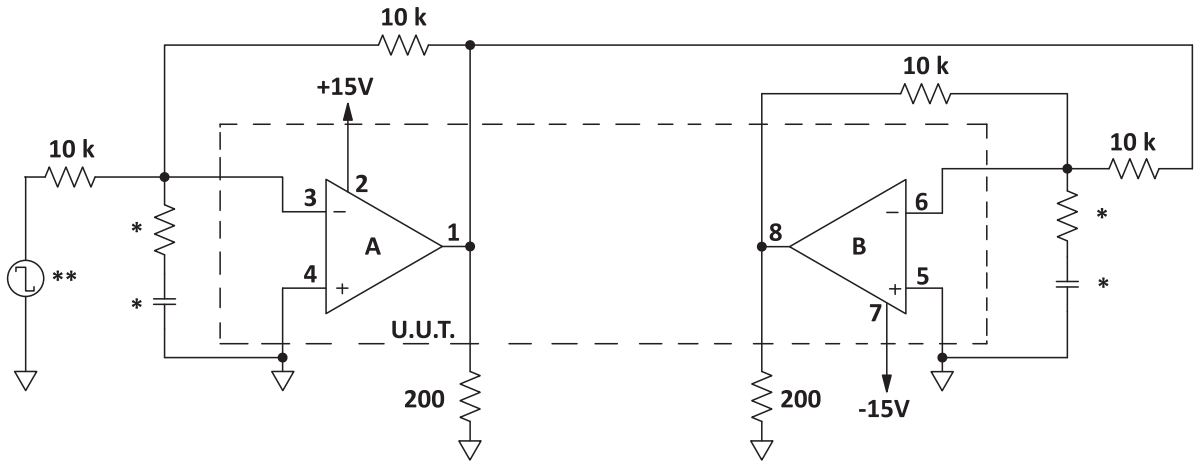
Table 4 Group A Inspection

SG	Parameter	Symbol	Temp.	Power	Test Conditions	Min	Max	Units
1	Quiescent Current	I_Q	25°C	±15	V_{IN} = 0, A_V = 100		30	mA
1	Input Offset Voltage	V_{OS}	25°C	±2.5	V_{IN} = 0, A_V = 100		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±15	V_{IN} = 0, A_V = 100		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±20	V_{IN} = 0, A_V = 100		14	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±15	V_{IN} = 0		1000	nA
1	Input Bias Current, –IN	$-I_B$	25°C	±15	V_{IN} = 0		1000	nA
1	Input Offset Current	I_{OS}	25°C	±15	V_{IN} = 0		500	nA
3	Quiescent Current	I_Q	–55°C	±15	V_{IN} = 0, A_V = 100		30	mA
3	Input Offset Voltage	V_{OS}	–55°C	±2.5	V_{IN} = 0, A_V = 100		14	mV
3	Input Offset Voltage	V_{OS}	–55°C	±15	V_{IN} = 0, A_V = 100		14	mV
3	Input Offset Voltage	V_{OS}	–55°C	±20	V_{IN} = 0, A_V = 100		18	mV
3	Input Bias Current, +IN	$+I_B$	–55°C	±15	V_{IN} = 0		1000	nA
3	Input Bias Current, –IN	$-I_B$	–55°C	±15	V_{IN} = 0		1000	nA
3	Input Offset Current	I_{OS}	–55°C	±15	V_{IN} = 0		500	nA
2	Quiescent Current	I_Q	125°C	±15	V_{IN} = 0, A_V = 100		40	mA
2	Input Offset Voltage	V_{OS}	125°C	±2.5	V_{IN} = 0, A_V = 100		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±15	V_{IN} = 0, A_V = 100		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±20	V_{IN} = 0, A_V = 100		19	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±15	V_{IN} = 0		1000	nA
2	Input Bias Current, –IN	$-I_B$	125°C	±15	V_{IN} = 0		1000	nA
2	Input Offset Current	I_{OS}	125°C	±15	V_{IN} = 0		500	nA
4	Output Voltage, I_O = 2A	V_O	25°C	±9.5	R_L = 3 Ω	6.0		V
4	Output Voltage, I_O = 100mA	V_O	25°C	±11	R_L = 100 Ω	9.9		V
4	Output Voltage, I_O = 1A	V_O	25°C	±4.8	R_L = 3 Ω	2.8		V
4	Stability/Noise	E_N	25°C	±15	R_L = 500 Ω, A_V = 1 C_L = 1.5nF		1.0	mV
4	Crosstalk	XTLK	25°C	±15	R_L = 3 Ω	50		dB
4	Slew Rate	SR	25°C	±15	R_L = 500 Ω	0.5		V/µs
4	Open Loop Gain	A_{OL}	25°C	±15	R_L = 500 Ω, F = 10 Hz	75		dB
4	Common Mode Rejection	CMR	25°C	±17	R_L = 500 Ω, V_{CM} = ±14V	60		dB

SG	Parameter	Symbol	Temp.	Power	Test Conditions	Min	Max	Units
6	Output Voltage, I_O = 2A	V_O	–55°C	±9.5	R_L = 3 Ω	6.0		V
6	Output Voltage, I_O = 100mA	V_O	–55°C	±11	R_L = 100 Ω	9.9		V
6	Output Voltage, I_O = 1A	V_O	–55°C	±4.8	R_L = 3 Ω	2.8		V
6	Stability/Noise	E_N	–55°C	±15	R_L = 500 Ω, A_V = 1, C_L = 1.5nF		1.0	mV
6	Slew Rate	SR	–55°C	±15	R_L = 500 Ω	0.5		V/µs
6	Open Loop Gain	A_{OL}	–55°C	±15	R_L = 500 Ω, F = 10 Hz	75		dB
6	Common Mode Rejection	CMR	–55°C	±17	R_L = 500 Ω, V_{CM} = ±14V	60		dB
5	Output Voltage, I_O = 1A	V_O	125°C	±4.8	R_L = 3 Ω	2.8		V
5	Output Voltage, I_O = 100mA	V_O	125°C	±11	R_L = 100 Ω	9.9		V
5	Output Voltage, I_O = 750mA	V_O	125°C	±4.0	R_L = 3 Ω	2.25		V
5	Stability/Noise	E_N	125°C	±15	R_L = 500 Ω, A_V = 1, C_L = 1.5nF		1.0	mV
5	Slew Rate	SR	125°C	±15	R_L = 500 Ω	0.5		V/µs
5	Open Loop Gain	A_{OL}	125°C	±15	R_L = 500 Ω, F = 10 Hz	75		dB
5	Common Mode Rejection	CMR	125°C	±17	R_L = 500 Ω, V_{CM} = ±14V	60		dB

BURN IN CIRCUIT

Figure 1: Burn in Circuit



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.
** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C